

Refine Search

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adjacent near10 (TFT near10 capacitor)	61

Database:

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Search:

L25

Search History

 DATE: Tuesday, February 14, 2006 [Printable Copy](#) [Create Case](#)

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	DB=USPT; PLUR=YES; OP=OR		
<u>L25</u>	adjacent near10 (TFT near10 capacitor)	61	<u>L25</u>
	DB=PGPB; PLUR=YES; OP=OR		
<u>L24</u>	adjacent near10 (TFT near10 capacitor)	40	<u>L24</u>
<u>L23</u>	L22 and (((dielectric near5 thickness) near10 "same") same ("gate dielectric" or "gate insulation"))	0	<u>L23</u>
<u>L22</u>	TFT same capacitor	4547	<u>L22</u>
	DB=USPT; PLUR=YES; OP=OR		
<u>L21</u>	L20 and (("gate electrode" near10 "conductivity type") same (capacitor near6 (electrode or plate)))	0	<u>L21</u>
<u>L20</u>	L15 and (((dielectric near5 thickness) near10 "same") same ("gate dielectric" or "gate insulation"))	6	<u>L20</u>
<u>L19</u>	L15 (((dielectric near5 thickness) near10 "same") same ("gate dielectric" or "gate insulation"))	3728	<u>L19</u>

<u>L18</u>	L15 same ("same conductivity" near10 (active) same (capacit\$5 near5 (plate or electrode)))	1	<u>L18</u>
<u>L17</u>	L15 and ("same conductivity" near10 (active) near10 (capacit\$5 near5 (plate or electrode)))	0	<u>L17</u>
<u>L16</u>	L15 ("same conductivity" near10 (active) near10 (capacit\$5 near5 (plate or electrode)))	3567	<u>L16</u>
<u>L15</u>	TFT same capacitor	3567	<u>L15</u>
<u>L14</u>	"quantum well" near16 (InGaN near5 thickness) near20 AlInGaN	0	<u>L14</u>
<u>L13</u>	L7 and (Al near7 (composition or percentage or concentration))	4	<u>L13</u>
<u>L12</u>	"quantum well" near13 (InGaN near5 thickness) near15 AlInGaN	0	<u>L12</u>
<u>L11</u>	L9 and thickness	7	<u>L11</u>
<u>L10</u>	L6 and thickness	14	<u>L10</u>
<u>L9</u>	L7 and (In near7 (composition or percentage or concentration))	7	<u>L9</u>
<u>L8</u>	L7 and (In near7 (composition or percentage))	5	<u>L8</u>
<u>L7</u>	L2 and (("quantum well") same (InGaN) same AlInGaN)	14	<u>L7</u>
<u>L6</u>	L2 and (("quantum well") same (InGaN) same AlInGaN)	14	<u>L6</u>
<u>L5</u>	L2 and (multilayer\$5 same ("quantum well") same (InGaN) same AlInGaN)	0	<u>L5</u>
<u>L4</u>	L2 and (multilayer\$5 near4 ("quantum well"))	9	<u>L4</u>
<u>L3</u>	L2 and ("quantum well")	536	<u>L3</u>
<u>L2</u>	L1 and substrate	1194	<u>L2</u>
<u>L1</u>	("gallium nitride" or GaN) same LED	1321	<u>L1</u>

END OF SEARCH HISTORY